

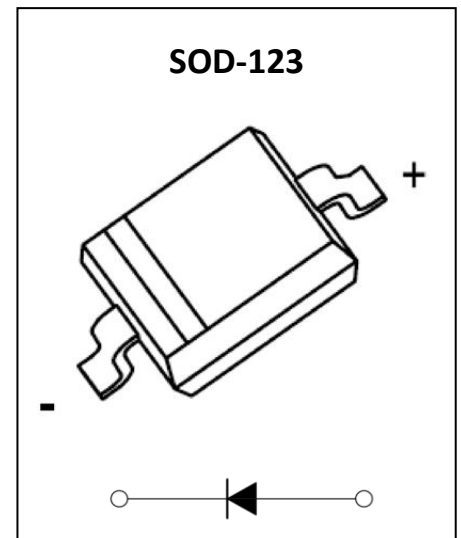
GP5818W Schottky Barrier Diode

Feature

- Small power mold type
- Low VF
- Low IR
- High reliability

Application

- High frequency inverters
- Free wheeling
- Polarity protection applications



MARKING:



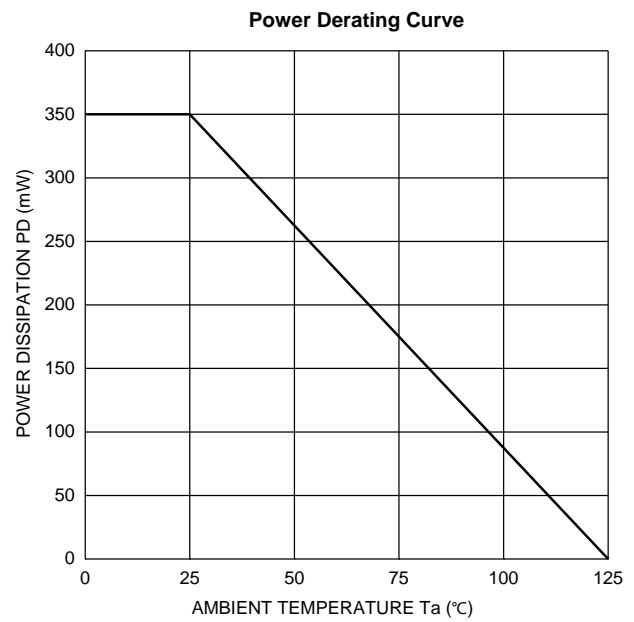
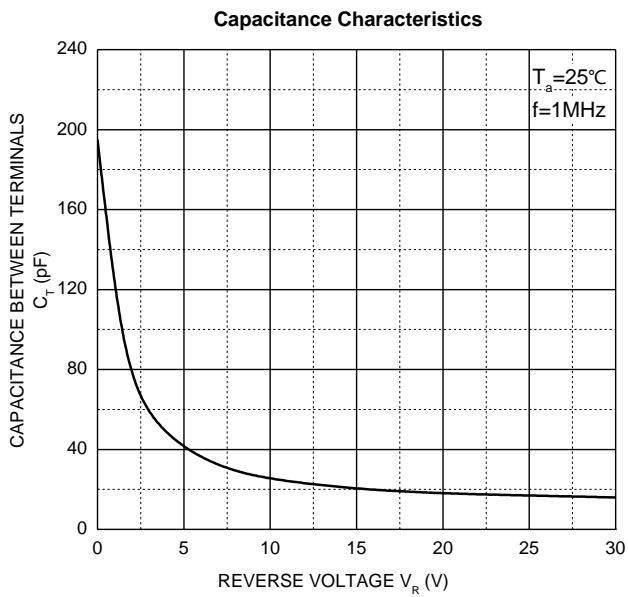
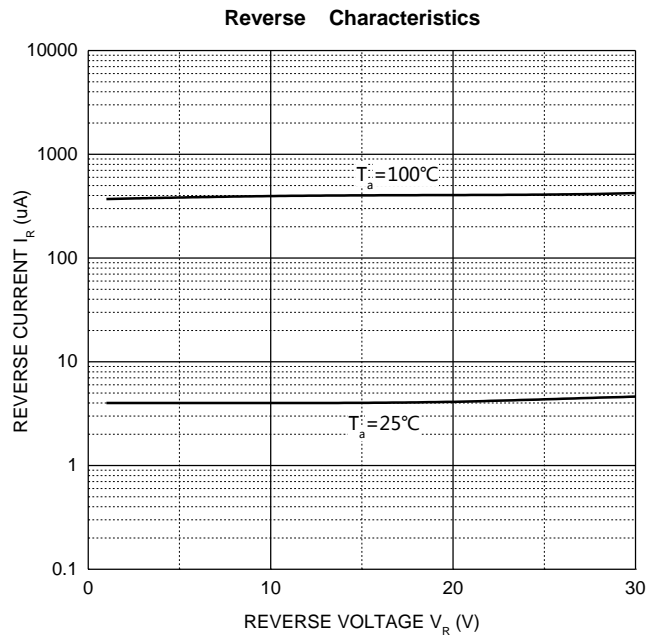
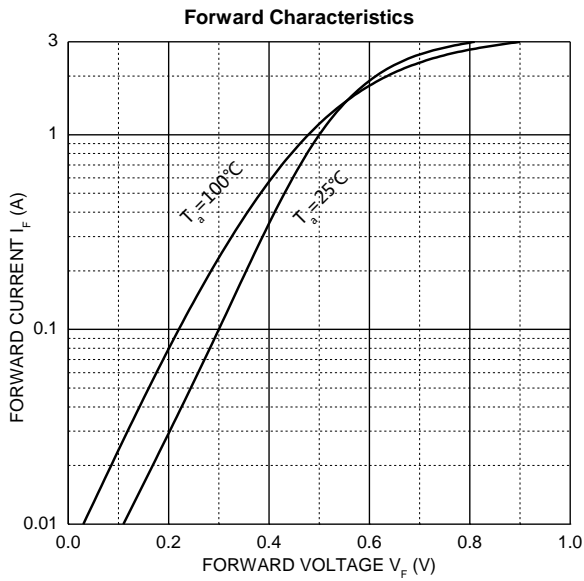
ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

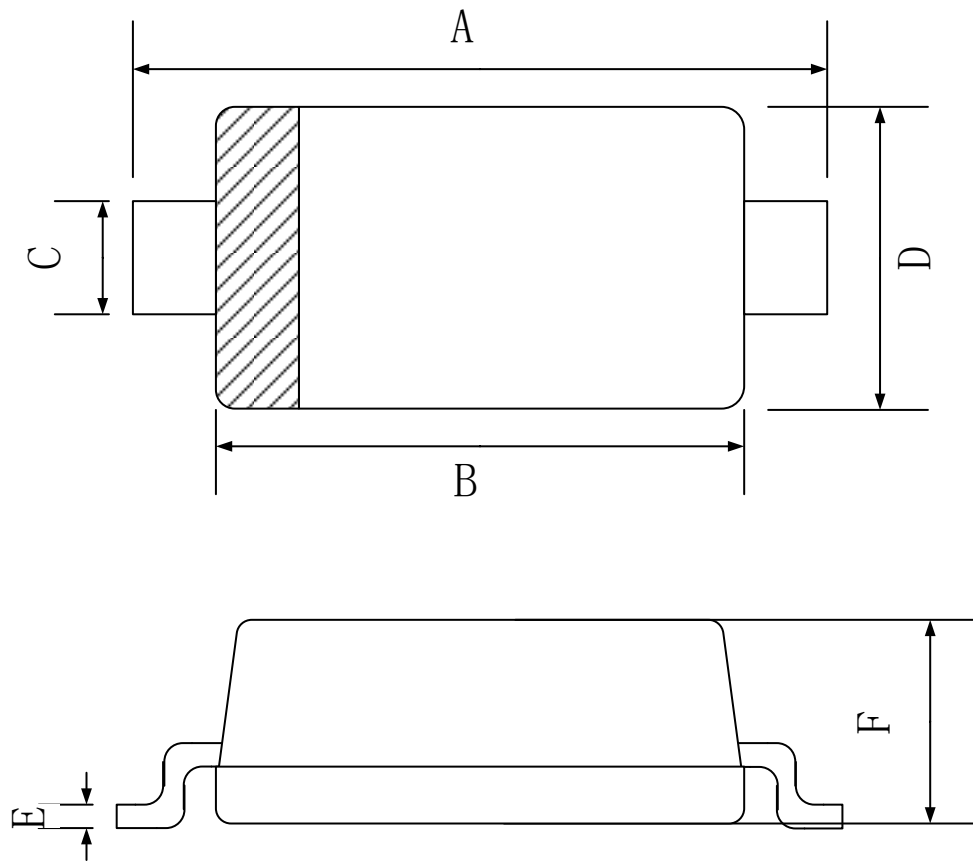
Parameter	Symbol	Value	Unit
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	1	A
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I _{FSM}	15	A
Power Dissipation	P _D	0.35	W
Thermal Resistance from Junction to Ambient	R _{θJA}	285	°C/W
Junction Temperature	T _J	125	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V _{BR}	I _R = 250μA	30	40		V
Forward voltage	V _F	I _F = 0.5A	0	0.40	0.45	V
		I _F = 1.0A	0	0.48	0.53	V
		I _F = 3.0A	0	0.73	0.85	V
Reverse current	I _R	V _R = 30V		3	50	μA
Diode capacitance	C _D	V _R = 4V, f = 1MHz		50		pF

Typical Characteristics



SOD-123 Package Outline Dimensions


Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	3.45	3.65	3.85
B	2.55	2.65	2.75
C	0.45	0.55	0.65
D	1.50	1.60	1.70
E	0.09	0.105	0.12
F	0.95	1.15	1.35

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)